

Low-Voltage Single SPDT Analog Switch

DESCRIPTION

The DG9411 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 9 ns, t_{OFF} : 5 ns), low on-resistance ($r_{DS(on)}$: 7 Ω) and small physical size (SC70), the DG9411 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9411 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-before - make is guaranteed for DG9411.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FEATURES

- Low voltage operation (2.25 V to 5.5 V)
- Low on-resistance $r_{DS(on)}$: 7 Ω
- Fast switching t_{ON}: 9 ns, t_{OFF}: 5 ns
- Low charge injection Q_{INJ}: 5 pC
- Low power consumption
- TTL/CMOS compatible
- 6-Pin SC70 package

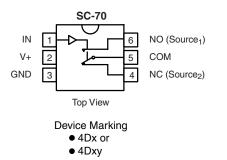
BENEFITS

- Reduced power consumption
- · Simple logic interface
- High accuracy
- Reduce board space

APPLICATIONS

- Cellular phones
- Communication systems
- Portable test equipment
- · Battery operated systems
- Sample and hold circuits

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABL	E	
Logic	NC	NO
0	ON	OFF
1	OFF	ON

 $\begin{array}{l} \mbox{Logic "0"} \leq 0.8 \ \mbox{V} \\ \mbox{Logic "1"} \geq 2.4 \ \mbox{V} \end{array}$

ORDERING INFORMATION						
Temp Range Package Part Number						
- 40 to 85 °C	SC70-6	DG9411DL-T1 DG9411DL-T1-E3				

* Pb containing terminations are not RoHS compliant, exemptions may apply.



COMPLIANT



ABSOLUTE MAXIMUM RATINGS							
Parameter		Limit	Unit				
Reference V+ to GND		- 0.3 to + 6	M				
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	v				
Continuous Current (Any Terminal)		± 50	mA				
Peak Current (Pulsed at 1 ms, 10 % c	luty cycle)	± 200	- IIIA				
Storage Temperature		- 65 to 150	°C				
Power Dissipation (Packages) ^b 6-Pin SC70 ^c		250	mW				

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board. c. Derate 3.1 mW/°C above 70 °C.

SPECIFICATIONS V+	= 2.5 V									
		Test Conditions Unless Otherwise Specified V+ = 2.5 V, ± 10 %		Limits - 40 to 85 °C		°C				
Parameter	Symbol	$V_{IN} = 0.4 \text{ or } 2.0 \text{ V}^{e}$	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit			
Analog Switch										
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	V			
Drain-Source On-Resistance	r _{DS(on)}	V+ = 2.25 V, V _D = 1.0 V, I _S = 10 mA	Room Full ^d		26 29	35 40	Ω			
r _{DS(on)} Flatness ^d	r _{DS(on)} Flatness	V+ = 2.5 V	Room		10		32			
Switch Off	I _{S(off)}	V+ = 2.75 V, V _S = 0.5 V/1.5 V, V _D = 1.5 V/0.5 V	Room Full ^d	- 250 - 3.0		250 3.0	pA nA			
Leakage Current [®]	I _{D(off)}		Room Full ^d	- 250 - 3.0		250 3.0	pA nA			
Channel-On Leakage Current ^f	I _{D(on)}	V+ = 2.75 V, V _S = V _D = 0.5 V/1.5 V	Room Full ^d	- 250 - 3.0		250 3.0	pA nA			
Digital Control										
Input High Voltage	V _{INH}		Full	2			v			
Input Low Voltage	V _{INL}		Full			0.4	v			
Input Capacitance ^d	C _{in}		Full		3		pF			
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA			
Dynamic Characteristics										
Turn-On Time	t _{ON}		Room Full ^d		16	40 45				
Turn-Off Time	t _{OFF}	$V^{}_{D}$ or $V^{}_{S}$ = 1.5 V, $R^{}_{L}$ = 300 $\Omega,~C^{}_{L}$ = 35 pF Figures 1 and 2	Room Full		7	23 28	ns			
Break-Before-Make Time	t _d		Room ^d	1	12					
Charge Injection ^d	Q _{INJ}	C_{L} = 1 nF, V_{GEN} = 0 V, V_{S} = 0 V, R_{GEN} = 0 $\Omega,$ Figure 3	Room		5	10	рС			
Off-Isolation ^d	OIRR	$R_{I} = 50 $ Ω, $C_{I} = 5 $ pF, f = 1 MHz	Room		- 73		dB			
Crosstalk ^d	X _{TALK}	11 - 30 $22 $ $01 - 3 $ $01 $ $1 - 1 $ $101 $ 12	Room		- 70		uВ			
Source-Off Capacitance ^d	C _{S(off)}		Room		7					
Channel-On Capacitance ^d	C _{D(on)}	$V_{IN} = 0$ or V+, f = 1 MHz	Room		20		pF			
Drain-to-Source Capacitance ^d	C _{DS(off)}		Room		20					
Power Supply										
Power Supply Range	V+			2.25		2.75	V			
Power Supply Current ^d	I+ V _{IN} = 0 or V+				0.01	1.0	μA			
Power Consumption	P _C	- v _{IN} = 0 01 v+				0.3	μW			



		Test Conditions Unless Otherwise Specified		Limits - 40 to 85 °C			
Parameter	Symbol	V+ = 3 V, ± 10 % V _{IN} = 0.4 or 2.0 V ^e	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Analog Switch						<u> </u>	•
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	v
Drain-Source On-Resistance ^d	r _{DS(on)}	V+ = 2.7 V, V _D = 1.5 V, I _S = 10 mA	Room Full		15 19	25 30	Ω
r _{DS(on)} Flatness ^d	r _{DS(on)} Flatness	$V_{\rm S}$ = 0 to V+, I _S = 10 mA	Room		7.5		52
Switch Off	I _{S(off)}	V+ = 3.3 V, V _S = 1 V/3 V, V _D = 3 V/1 V	Room Full	- 500 - 4.0		500 4.0	pA nA
Leakage Current ^f	I _{D(off)}	v+ = 0.0 v, vg = + v/0 v, vD = 0 v/+ v	Room Full	- 500 - 4.0		500 4.0	pA nA
Channel-On Leakage Current ^f	I _{D(on)}	V+ = 3.3 V, V _S = V _D = 1 V/3 V	Room Full	- 500 - 4.0		500 4.0	pA nA
Digital Control	- -						
Input High Voltage	V _{INH}		Full	2			v
Input Low Voltage	V _{INL}		Full			0.8	V
Input Capacitance ^d	C _{in}		Full		3		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}		Room Full		12	15 20	
Turn-Off Time ^d	t _{OFF}	V_D or V_S = 2.0 V, R_L = 300 $\Omega,~C_L$ = 35 pF Figures1 and 2	Room Full		6	8 10	ns
Break-Before-Make Time ^d	t _d		Room	1	7		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, V_S = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	рС
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega_1 C_1 = 5 pF_1 f = 1 MHz$	Room		- 73		
Crosstalk ^d	X _{TALK}	$H_{L} = 50.52, G_{L} = 5.01, T = 1.0012$	Room		- 70		dB
Source-Off Capacitanced	C _{S(off)}		Room		7		
Channel-On Capacitance ^d	C _{D(on)}	$V_{IN} = 0$ or V+, f = 1 MHz	Room		20		pF
Drain-to-Source Capacitance ^d	C _{DS(off)}		Room		20		
Power Supply	<u> </u>						
Power Supply Range	V+			2.7		3.3	V
Power Supply Current	l+	V _{IN} = 0 or V+			0.01	1.0	μΑ
Power Consumption	P _C					0.4	μW



		Test Conditions Unless Otherwise Specified		-	Limits 40 to 85 °	Limits 0 to 85 °C	
		$V_{+} = 5 V, \pm 10 \%$					
Parameter	Symbol	V _{IN} = 0.8 or 2.4 V ^e	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Analog Switch			1		1		1
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	v
Drain-Source On-Resistance	r _{DS(on)}	V+ = 4.5 V, V _D = 3 V, I _S = 10 mA	Room Full		7 10	12 16	Ω
r _{DS(on)} Flatness ^d	r _{DS(on)} Flatness	V+ = 2.5 V	Room		2		52
Switch Off	I _{S(off)}	V+ = 5.5 V, V _S = 1 V/4.5 V, V _D = 4.5 V/1 V	Room Full	- 1.0 - 4.0		1.0 4.0	
Leakage Current	I _{D(off)}	v = 0.0 v, vg = 1 v/4.0 v, vg = 4.0 v/1 v	Room Full	- 1.0 - 4.0		1.0 4.0	nA
Channel-On Leakage Current	I _{D(on)}	V+ = 5.5 V, V _S = V _D = 1 V/4.5 V	Room Full	- 1.0 - 3.0		1.0 4.5	
Digital Control							
Input High Voltage	V _{INH}		Full	2.4			v
Input Low Voltage	V _{INL}		Full			0.8	v
Input Capacitance	C _{in}		Full		3		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V_{D} or V_{S} = 3 V, R_{I} = 300 Ω , C_{I} = 35 pF	Room Full		9	11 15	
Turn-Off Time ^d	t _{OFF}	V_D or $V_S = 3 V$, $H_L = 300 \Omega$, $C_L = 35 pF$ Figure 1 and 2	Room Full		5	7 9	ns
Break-Before-Make Time ^d	t _d		Room	1	4		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_S = 0 V, V_{GEN} = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	рС
Off-Isolation ^d	OIRR		Room		- 73		
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 70		dB
Source-Off Capacitance ^d	C _{S(off)}		Room		7		
Channel-On Capacitance ^d	C _{D(on)}	$V_{IN} = 0$ or V+, f = 1 MHz	Room		20		pF
Drain-to-Source Capacitance ^d	C _{DS(off)}	$v_{\rm IN} = 0$ or $v_{\rm T}$, $r = 1$ with 2	Room		20		p
Power Supply							
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	l+	V – 0 or V±			0.01	1.0	μA
Power Consumption P _C		V _{IN} = 0 or V+				0.6	μW

Notes:

a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

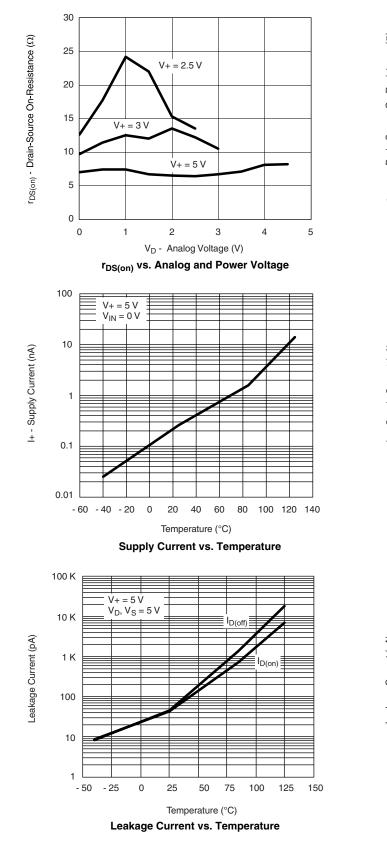
f. Guaranteed by 5 V leakage testing, not production tested.

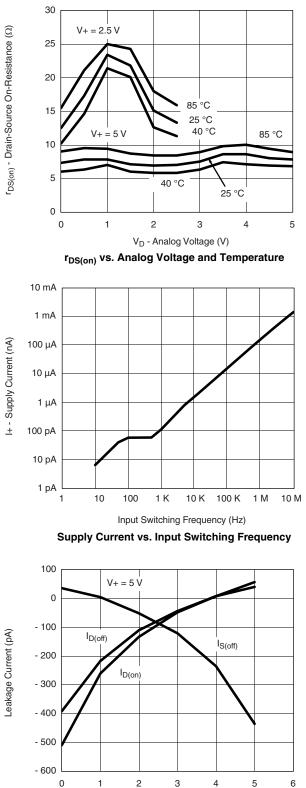
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



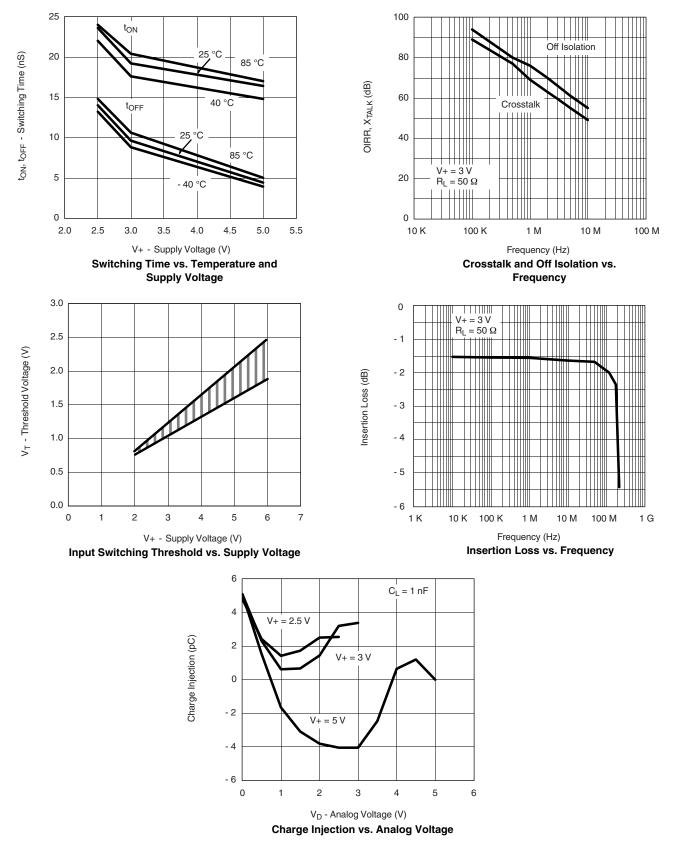


Document Number: 71347 S-72609-Rev. D, 24-Dec-07 V_D, V_S - Analog Voltage (V)

Leakage vs. Analog Voltage



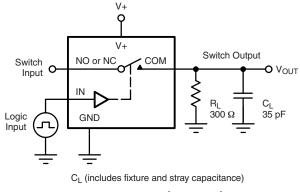
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



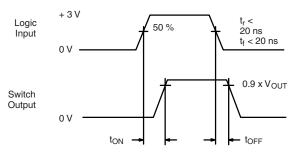


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TEST CIRCUITS

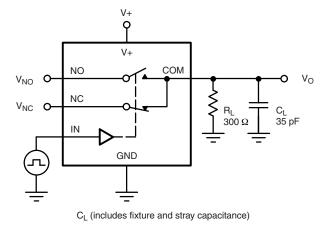






Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.





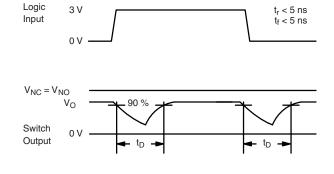
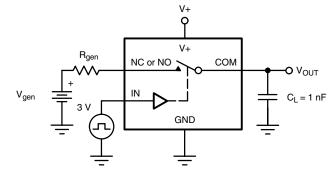
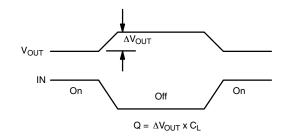


Figure 2. Break-Before-Make Interval





IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

DG9411

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TEST CIRCUITS

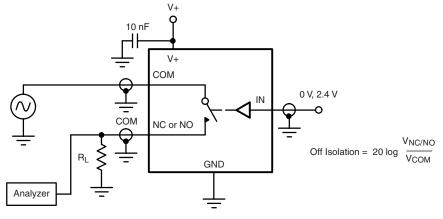


Figure 4. Off-Isolation

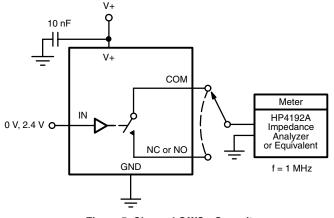


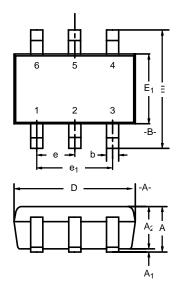
Figure 5. Channel Off/On Capacitance

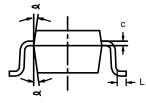
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Package Information Vishay Siliconix

SC-70: 6-LEADS





	MIL	LIMET	ERS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.90	-	1.10	0.035	-	0.043	
A ₁	-	-	0.10	-	-	0.004	
A ₂	0.80	-	1.00	0.031	-	0.039	
b	0.15	-	0.30	0.006	-	0.012	
С	0.10	-	0.25	0.004	-	0.010	
D	1.80	2.00	2.20	0.071	0.079	0.087	
E	1.80	2.10	2.40	0.071	0.083	0.094	
E ₁	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65BSC			0.026BSC	;	
e ₁	1.20	1.30	1.40	0.047	0.051	0.055	
L	0.10	0.20	0.30	0.004	0.008	0.012	
٩	X 7°Nom 7°Nom						
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550							



Vishay

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